

IRLR8256PbF
IRLU8256PbF

HEXFET® Power MOSFET

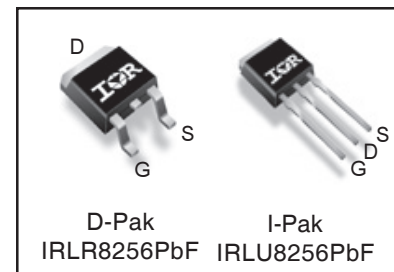
Applications

- High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use

V_{DSS}	R_{DS(on)} max	Qg
25V	5.7mΩ	10nC

Benefits

- Very Low RDS(on) at 4.5V V_{GS}
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current
- Lead-Free
- RoHS compliant



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

	Parameter	Max.	Units
V _{DS}	Drain-to-Source Voltage	25	V
V _{GS}	Gate-to-Source Voltage	± 20	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	81 ^④	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	57 ^④	
I _{DM}	Pulsed Drain Current ^①	325	
P _D @ T _C = 25°C	Maximum Power Dissipation ^②	63	W
P _D @ T _C = 100°C	Maximum Power Dissipation ^②	31	
	Linear Derating Factor	0.42	W/°C
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ^③	—	2.4	°C/W
R _{θJA}	Junction-to-Ambient (PCB Mount) ^⑤	—	50	
R _{θJA}	Junction-to-Ambient	—	110	

ORDERING INFORMATION:

See detailed ordering and shipping information on the last page of this data sheet.

Notes ^① through ^⑥ are on page 11

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	25	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	18	—	mV/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	4.2	5.7	mΩ	$V_{GS} = 10V, I_D = 25A$ ③
		—	6.7	8.5		$V_{GS} = 4.5V, I_D = 20A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	1.8	2.35	V	$V_{DS} = V_{GS}, I_D = 25\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-7.2	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	81	—	—	S	$V_{DS} = 13V, I_D = 20A$
Q_g	Total Gate Charge	—	10	15	nC	$V_{DS} = 13V$ $V_{GS} = 4.5V$ $I_D = 20A$ See Fig. 16
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	2.3	—		
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	1.6	—		
Q_{gd}	Gate-to-Drain Charge	—	3.6	—		
Q_{godr}	Gate Charge Overdrive	—	2.6	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	5.1	—		
Q_{oss}	Output Charge	—	9.0	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
R_G	Gate Resistance	—	2.5	3.9	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	9.7	—	ns	$V_{DD} = 13V, V_{GS} = 4.5V$ ③ $I_D = 20A$ $R_G = 1.8\Omega$ See Fig. 14
t_r	Rise Time	—	46	—		
$t_{d(off)}$	Turn-Off Delay Time	—	12	—		
t_f	Fall Time	—	8.5	—		
C_{iss}	Input Capacitance	—	1470	—	pF	$V_{GS} = 0V$ $V_{DS} = 13V$ $f = 1.0MHz$
C_{oss}	Output Capacitance	—	453	—		
C_{rss}	Reverse Transfer Capacitance	—	185	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	86	mJ
I_{AR}	Avalanche Current ①	—	20	A
E_{AR}	Repetitive Avalanche Energy ①	—	6.3	mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	81 ④	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	325		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 20A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	19	29	ns	$T_J = 25^\circ\text{C}, I_F = 20A, V_{DD} = 13V$
Q_{rr}	Reverse Recovery Charge	—	17	26	nC	$di/dt = 250A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

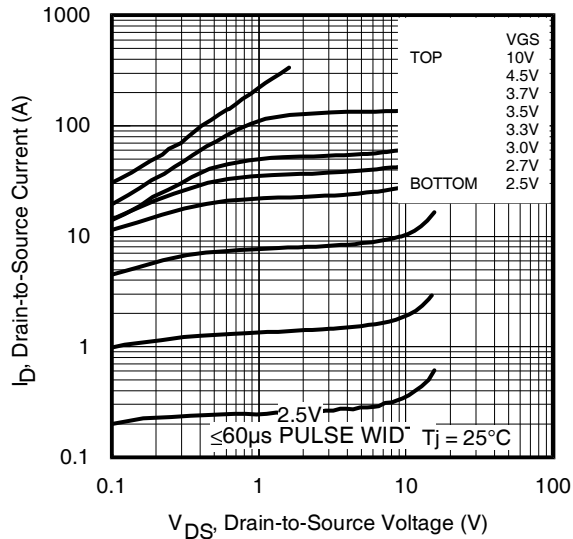


Fig 1. Typical Output Characteristics

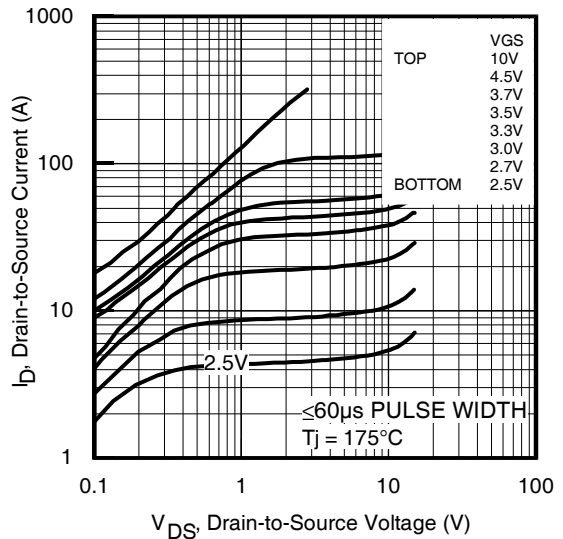


Fig 2. Typical Output Characteristics

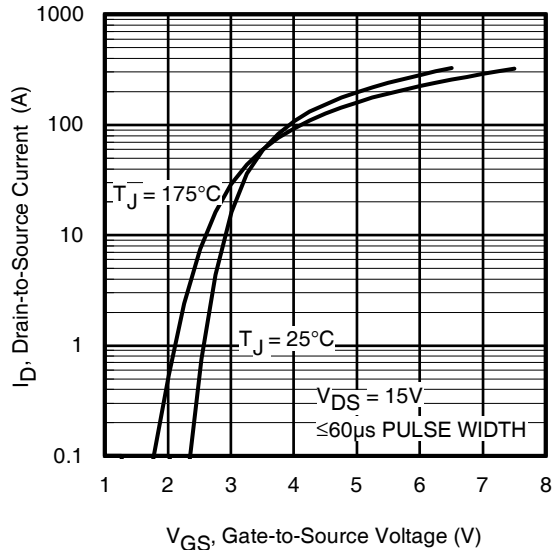


Fig 3. Typical Transfer Characteristics

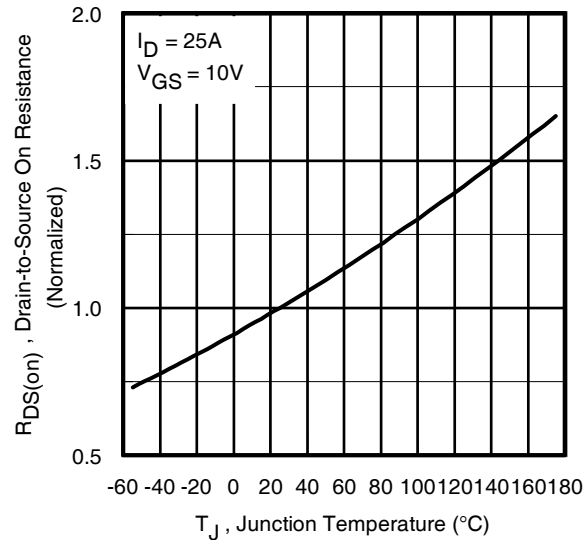


Fig 4. Normalized On-Resistance vs. Temperature

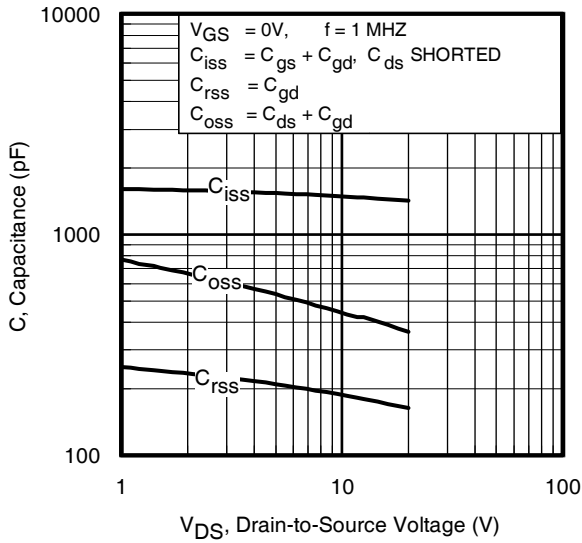


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

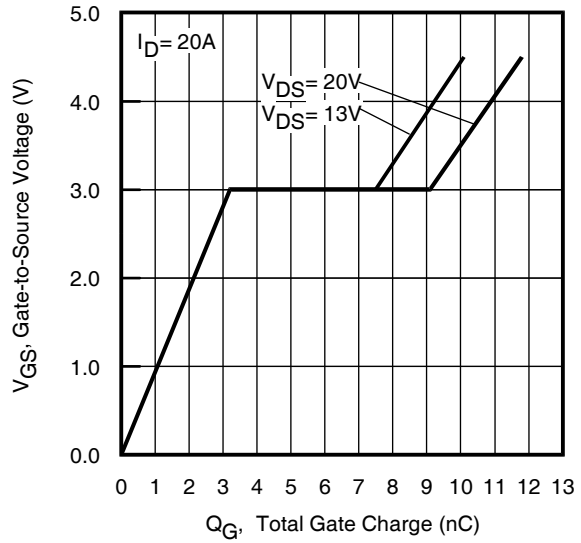


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

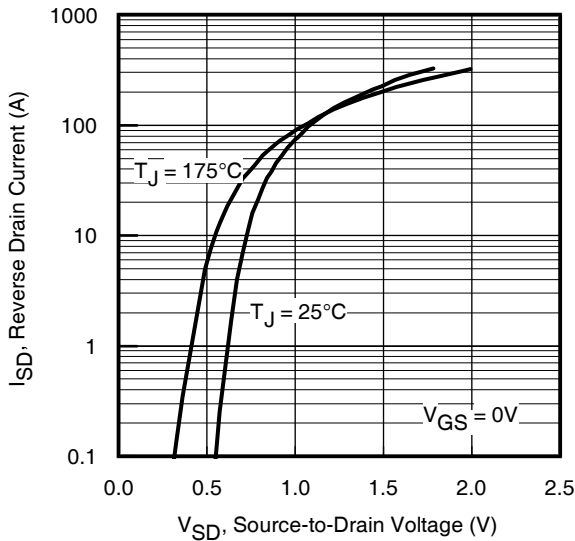


Fig 7. Typical Source-Drain Diode Forward Voltage

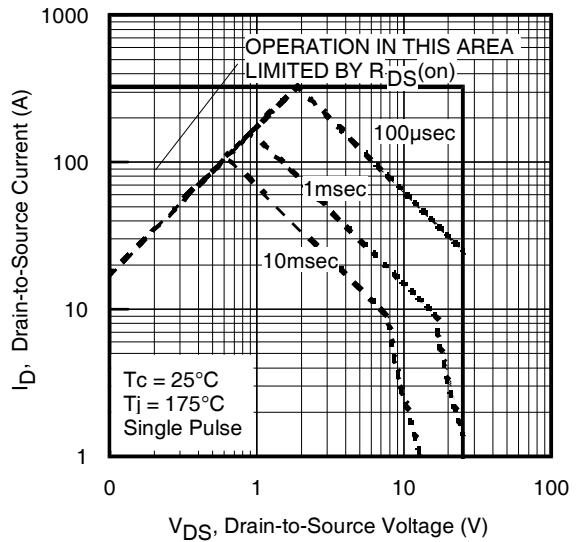


Fig 8. Maximum Safe Operating Area

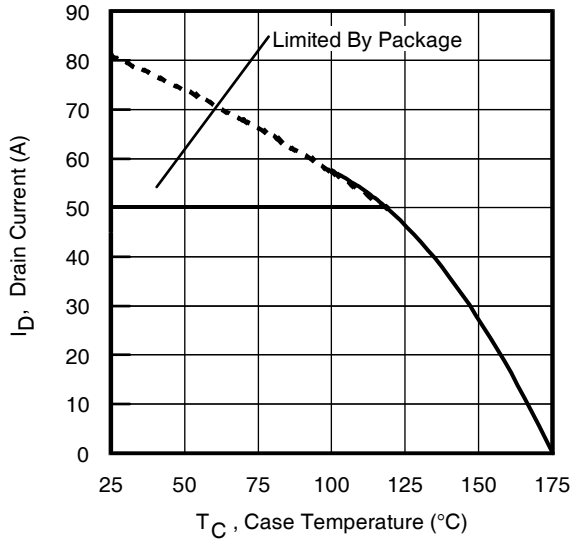


Fig 9. Maximum Drain Current vs. Case Temperature

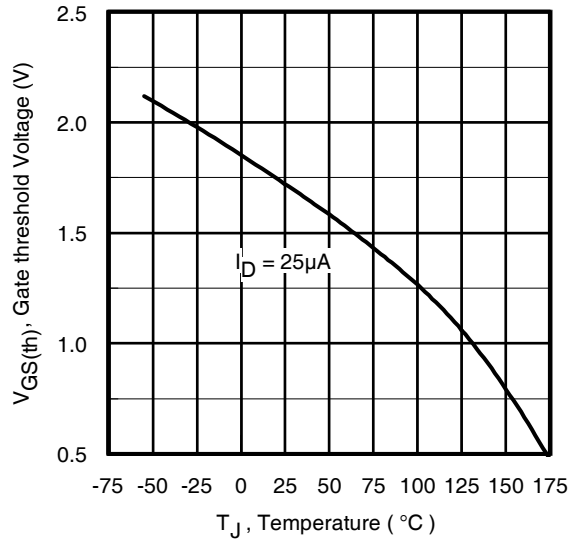


Fig 10. Threshold Voltage vs. Temperature

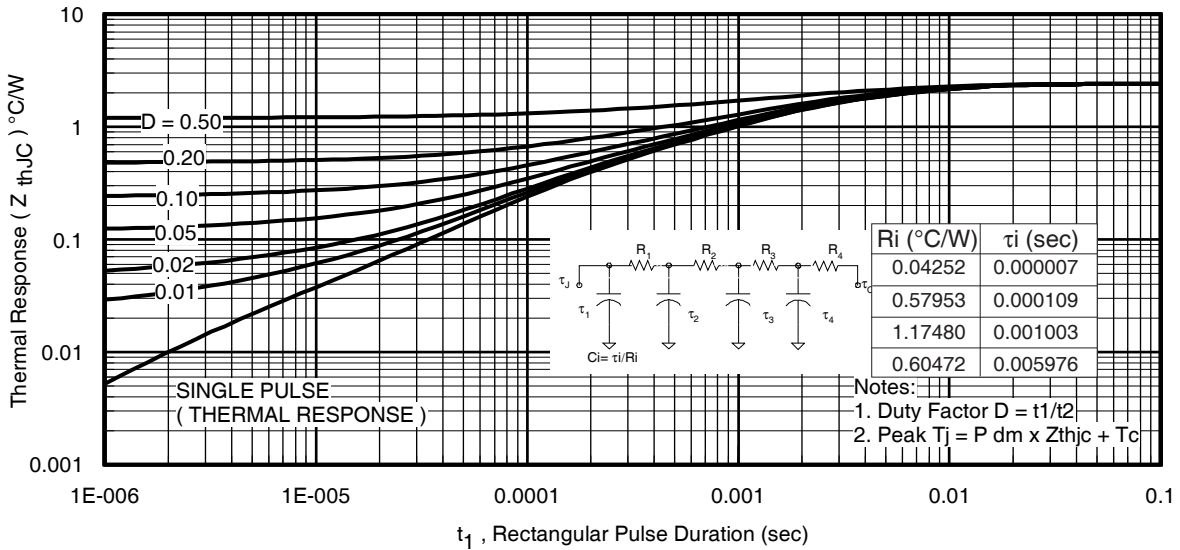


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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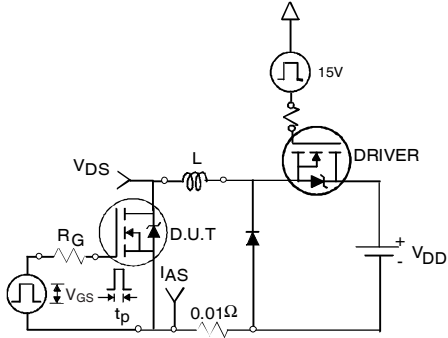


Fig 12a. Unclamped Inductive Test Circuit

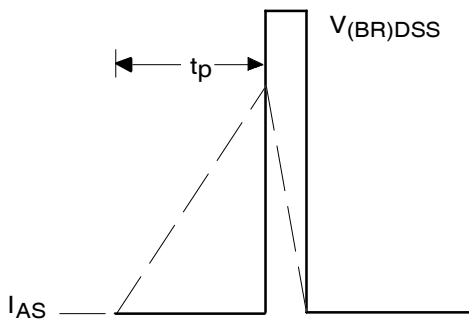


Fig 12b. Unclamped Inductive Waveforms

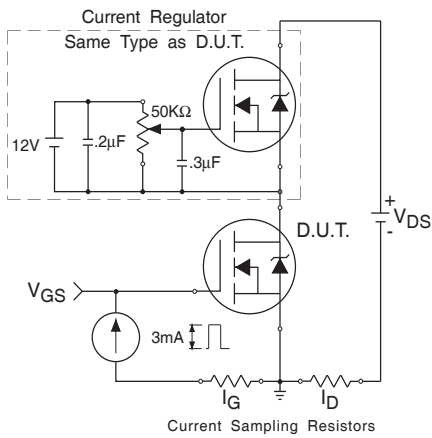


Fig 13. Gate Charge Test Circuit

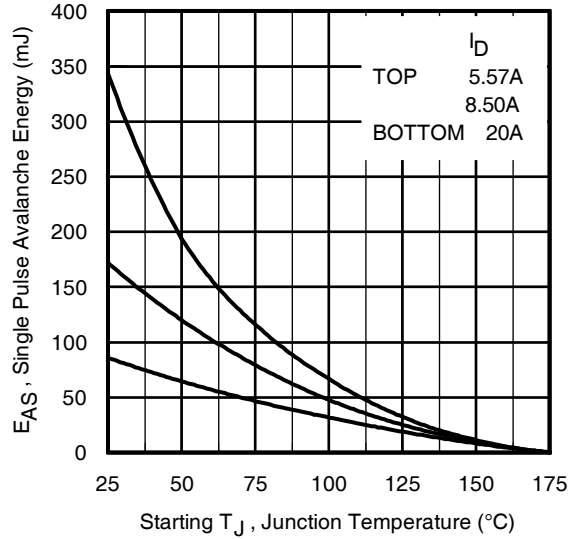


Fig 12c. Maximum Avalanche Energy vs. Drain Current

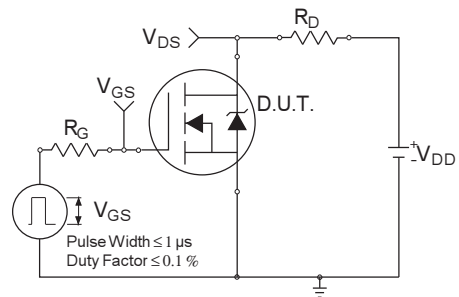


Fig 14a. Switching Time Test Circuit

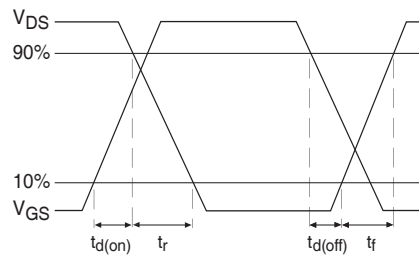


Fig 14b. Switching Time Waveforms

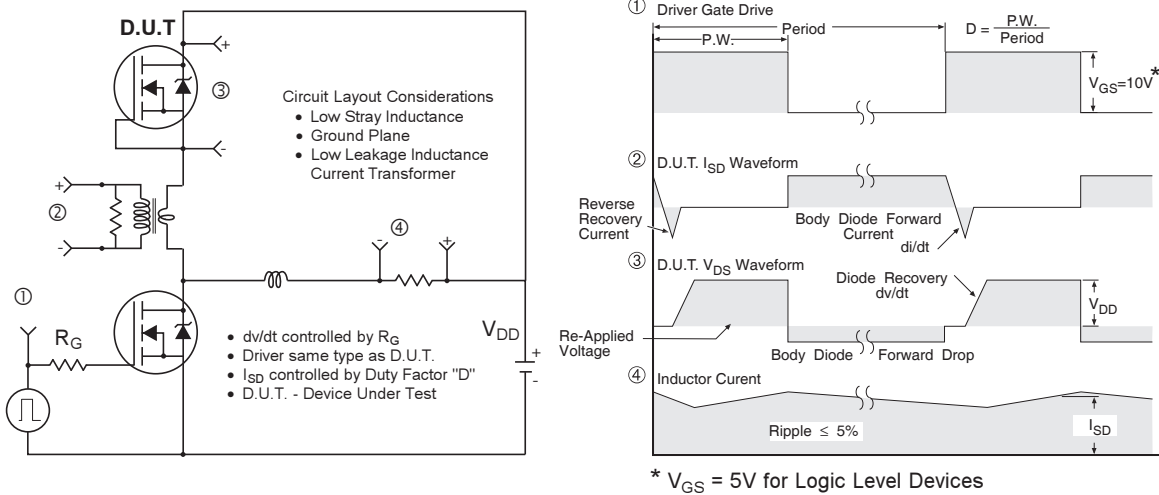


Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

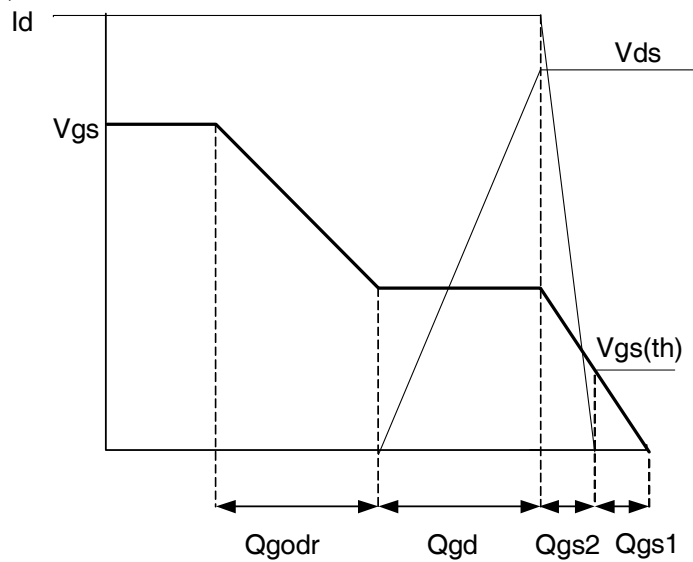
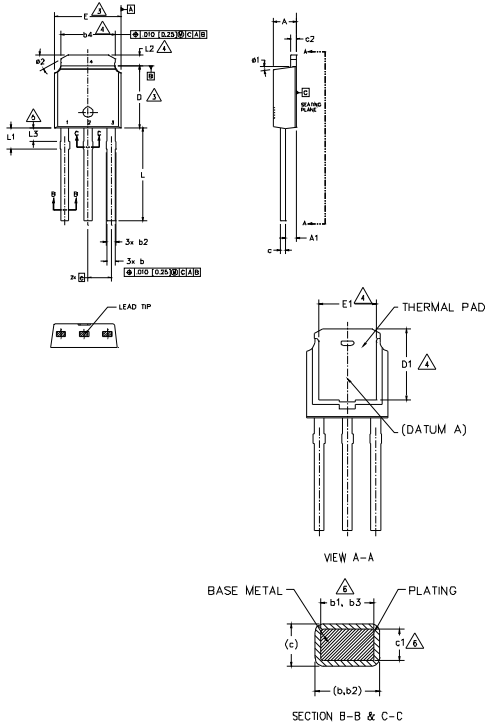


Fig 16. Gate Charge Waveform

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I-Pak (TO-251AA) Package Outline
 Dimensions are shown in millimeters (inches)

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- NOTES
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
 - 3.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - 4.- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
 - 5.- LEAD DIMENSION UNCONTROLLED IN L3.
 - 6.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
 - 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
 - 8.- CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	0.89	1.14	.035	.045	
b	0.64	0.89	.025	.035	6
b1	0.65	0.79	.025	.031	
b2	0.76	1.14	.030	.045	
b3	0.76	1.04	.030	.041	6
b4	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	6
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	3
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	3
E1	4.32	-	.170	-	4
e	2.29 BSC	-	.090 BSC	-	
L	8.89	9.65	.350	.380	
L1	1.91	2.29	.045	.090	
L2	0.89	1.27	.035	.050	4
L3	1.14	1.52	.045	.060	5
ø1	0	15	0	15	
ø2	25	35	25	35	

LEAD ASSIGNMENTS

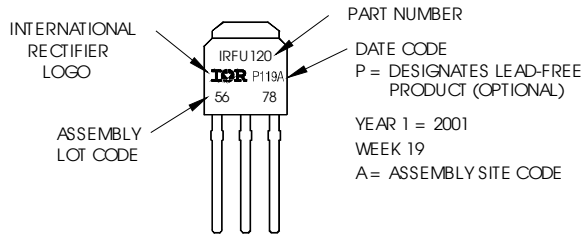
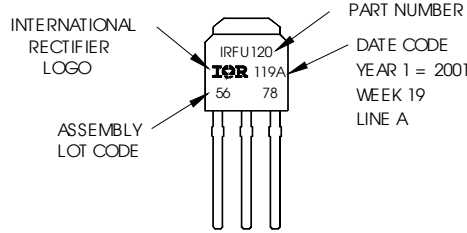
- HEXFET
- 1.- GATE
 - 2.- DRAIN
 - 3.- SOURCE
 - 4.- DRAIN

I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
 WITH ASSEMBLY
 LOT CODE 5678
 ASSEMBLED ON WW 19, 2001
 IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
 indicates Lead-Free

OR



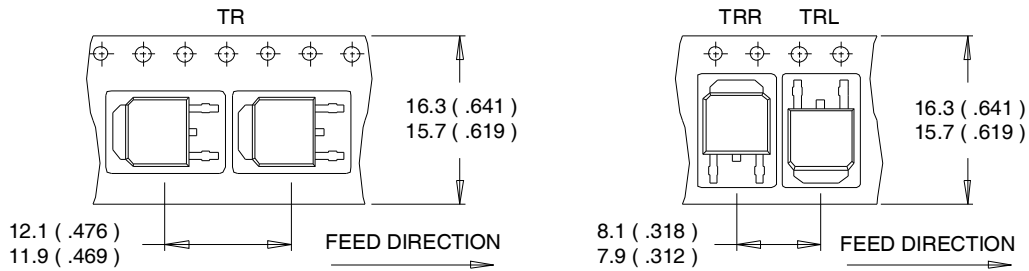
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>
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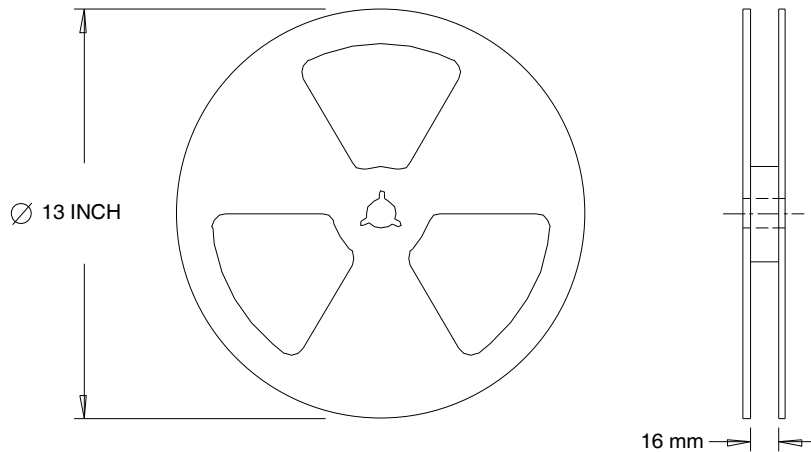
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRLR8256PBF	D-PAK	Tube/Bulk	75	
IRLR8256TRPBF	D-PAK	Tape and Reel	2000	
IRLR8256PBF	I-PAK	Tube/Bulk	75	

Qualification Information[†]

Qualification level	Industrial ^{††}	
	(per JEDEC JESD47F ^{†††} guidelines)	
	Comments: This family of products has passed JEDEC's Industrial qualification. IR's Consumer qualification level is granted by extension of the higher Industrial level.	
Moisture Sensitivity Level	D-PAK	MSL1 (per JEDEC J-STD-020D ^{†††})
	I-PAK	Not applicable
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site <http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information: <http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting $T_J = 25^\circ\text{C}$, $L = 0.43\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 20\text{A}$.

③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.

④ Calculated continuous current based on maximum allowable junction temperature.

Package limitation current is 50A.

⑤ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

⑥ R_θ is measured at T_J approximately 90°C .

Data and specifications subject to change without notice.

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